

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

$$V_{CES} = 600V$$

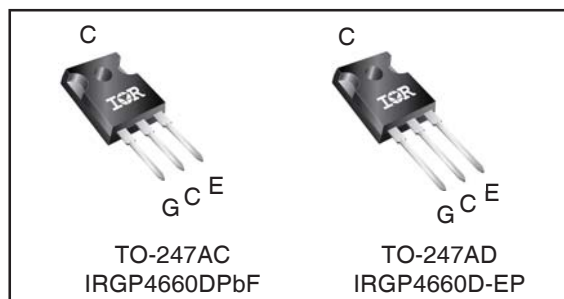
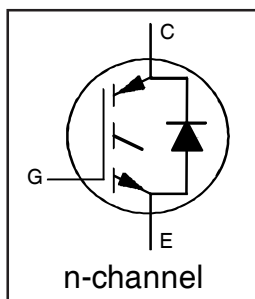
$$I_C = 60A, T_C = 100^{\circ}C$$

$$t_{SC} \geq 5\mu s, T_{J(max)} = 175^{\circ}C$$

$$V_{CE(on)} \text{ typ.} = 1.60V @ I_C = 48A$$

Applications

- Industrial Motor Drive
- Inverters
- UPS
- Welding



G	C	E
Gate	Collector	Emitter

Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High efficiency in a wide range of applications and switching frequencies
Square RBSOA and Maximum Junction Temperature 175°C	Improved reliability due to rugged hard switching performance and higher power capability
Positive $V_{CE(ON)}$ Temperature Coefficient	Excellent current sharing in parallel operation
5μs short circuit SOA	Enables short circuit protection scheme
Lead-Free, RoHS compliant	Environmentally friendly

Base part number	Package Type	Standard Pack		Orderable part number
		Form	Quantity	
IRGP4660DPbF	TO-247AC	Tube	25	IRGP4660DPbF
IRGP4660D-EPbF	TO-247AD	Tube	25	IRGP4660D-EPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^{\circ}C$	Continuous Collector Current	100	A
$I_C @ T_C = 100^{\circ}C$	Continuous Collector Current	60	
I_{CM}	Pulse Collector Current, $V_{GE} = 15V$	144	
I_{LM}	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	192	
$I_F @ T_C = 25^{\circ}C$	Diode Continuous Forward Current	100	
$I_F @ T_C = 100^{\circ}C$	Diode Continuous Forward Current	60	V
I_{FM}	Diode Maximum Forward Current ④	192	
V_{GE}	Continuous Gate-to-Emitter Voltage	±20	V
	Transient Gate-to-Emitter Voltage	±30	
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	330	W
$P_D @ T_C = 100^{\circ}C$	Maximum Power Dissipation	170	
T_J	Operating Junction and	-55 to +175	$^{\circ}C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Junction-to-Case (IGBT) ②	—	—	0.45	$^{\circ}C/W$
$R_{\theta JC}$ (Diode)	Junction-to-Case (Diode) ②	—	—	0.92	
$R_{\theta CS}$	Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient (typical socket mount)	—	—	40	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 150\mu A$ ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.30	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1mA$ (25 $^\circ\text{C}$ -175 $^\circ\text{C}$)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.60	1.90	V	$I_C = 48A, V_{GE} = 15V, T_J = 25^\circ\text{C}$
		—	1.90	—		$I_C = 48A, V_{GE} = 15V, T_J = 150^\circ\text{C}$
		—	2.00	—		$I_C = 48A, V_{GE} = 15V, T_J = 175^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	$V_{CE} = V_{GE}, I_C = 1.4mA$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-21	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 1.0mA$ (25 $^\circ\text{C}$ - 175 $^\circ\text{C}$)
g_{fe}	Forward Transconductance	—	32	—	S	$V_{CE} = 50V, I_C = 48A, PW = 80\mu s$
I_{CES}	Collector-to-Emitter Leakage Current	—	1.0	150	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	450	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.95	2.91	V	$I_F = 48A$
		—	1.45	—		$I_F = 48A, T_J = 175^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	95	140	nC	$I_C = 48A$
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	28	42		$V_{GE} = 15V$
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	35	53		$V_{CC} = 400V$
E_{on}	Turn-On Switching Loss	—	625	1141	μJ	$I_C = 48A, V_{CC} = 400V, V_{GE} = 15V$
E_{off}	Turn-Off Switching Loss	—	1275	1481		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH, T_J = 25^\circ\text{C}$
E_{total}	Total Switching Loss	—	1900	2622		Energy losses include tail & diode reverse recovery ⑤
$t_{d(on)}$	Turn-On delay time	—	60	78	ns	$I_C = 48A, V_{CC} = 400V, V_{GE} = 15V$
t_r	Rise time	—	40	56		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH, T_J = 25^\circ\text{C}$
$t_{d(off)}$	Turn-Off delay time	—	145	176		
t_f	Fall time	—	35	46		
E_{on}	Turn-On Switching Loss	—	1625	—	μJ	$I_C = 48A, V_{CC} = 400V, V_{GE} = 15V$
E_{off}	Turn-Off Switching Loss	—	1585	—		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH, T_J = 175^\circ\text{C}$
E_{total}	Total Switching Loss	—	3210	—		Energy losses include tail & diode reverse recovery ⑤
$t_{d(on)}$	Turn-On delay time	—	55	—	ns	$I_C = 48A, V_{CC} = 400V, V_{GE} = 15V$
t_r	Rise time	—	45	—		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH$
$t_{d(off)}$	Turn-Off delay time	—	165	—		$T_J = 175^\circ\text{C}$
t_f	Fall time	—	45	—		
C_{iss}	Input Capacitance	—	3025	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	245	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	90	—		$f = 1.0MHz$
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ\text{C}, I_C = 192A$ $V_{CC} = 480V, V_p = 600V$ $R_G = 10\Omega, V_{GE} = +15V$ to 0V
SCSOA	Short Circuit Safe Operating Area	5	—	—	μs	$V_{CC} = 400V, V_p = 600V$ $R_G = 10\Omega, V_{GE} = +15V$ to 0V
E_{rec}	Reverse Recovery Energy of the Diode	—	845	—	μJ	$T_J = 175^\circ\text{C}$
t_{rr}	Diode Reverse Recovery Time	—	115	—	ns	$V_{CC} = 400V, I_F = 48A$
I_{rr}	Peak Reverse Recovery Current	—	40	—	A	$V_{GE} = 15V, R_G = 10\Omega, L = 200\mu H, L_S = 150nH$

Notes:

- ① $V_{CC} = 80\% (V_{CES}), V_{GE} = 20V, L = 200\mu H, R_G = 10\Omega$.
- ② R_θ is measured at T_J of approximately 90 $^\circ\text{C}$.
- ③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
- ④ Pulse width limited by max. junction temperature.
- ⑤ Values influenced by parasitic L and C in measurement.

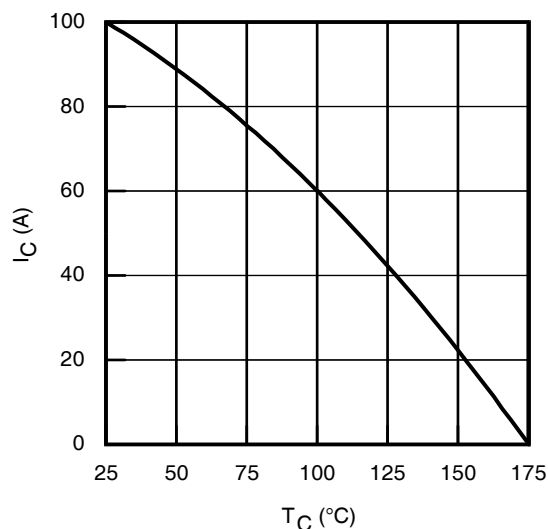


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

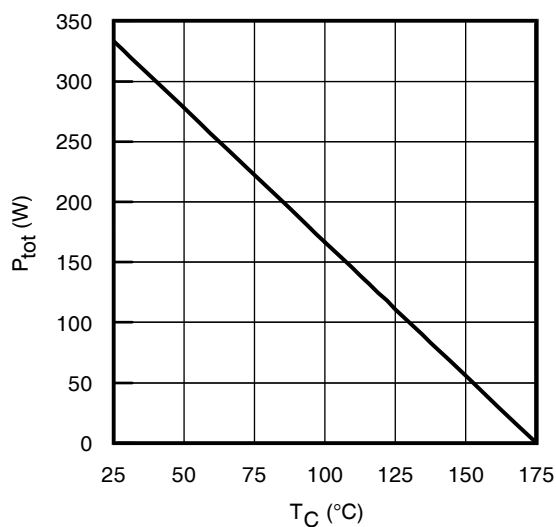


Fig. 2 - Power Dissipation vs. Case Temperature

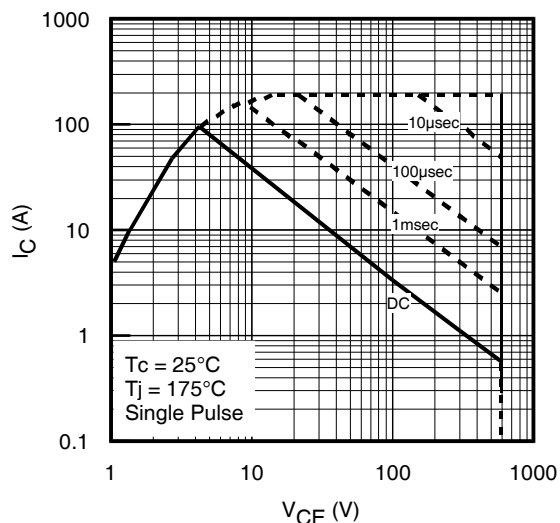


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$, $T_J \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

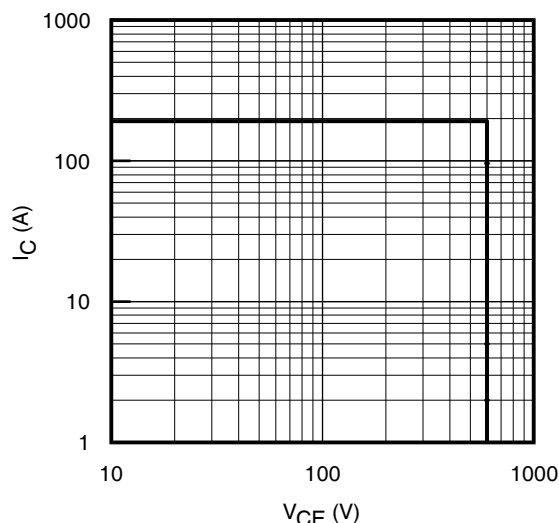


Fig. 4 - Reverse Bias SOA
 $T_J = 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

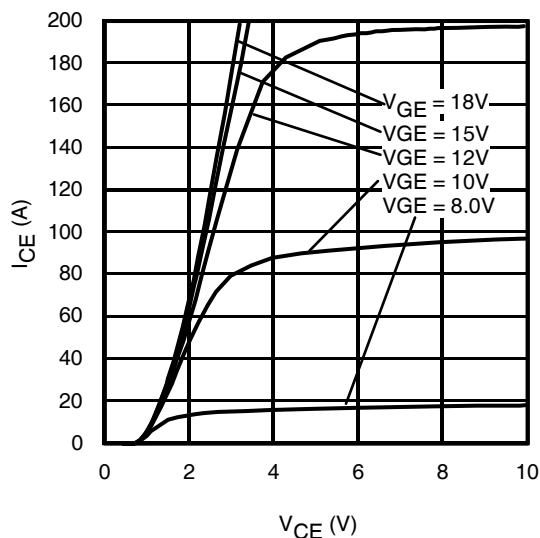


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 80\mu\text{s}$

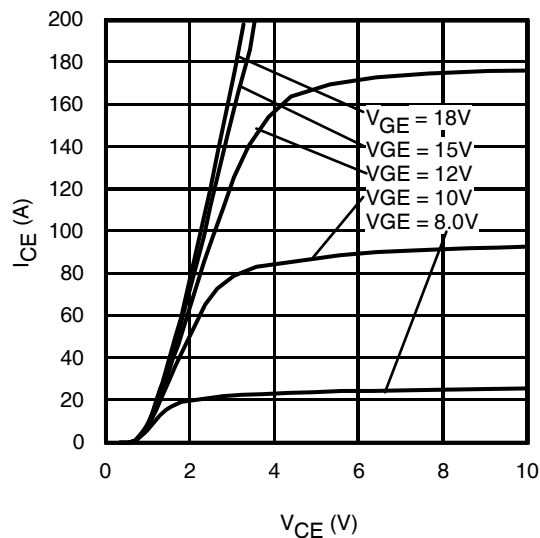


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 80\mu\text{s}$

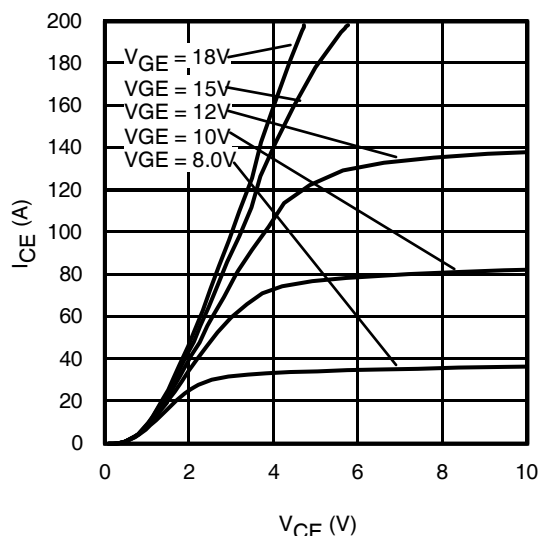


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 175^\circ\text{C}$; $t_p = 80\mu\text{s}$

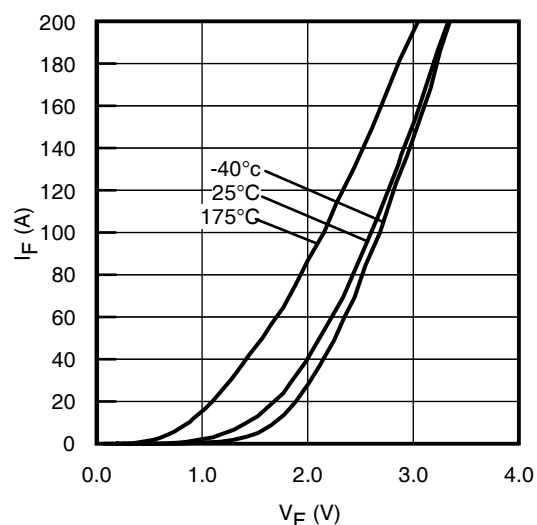


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

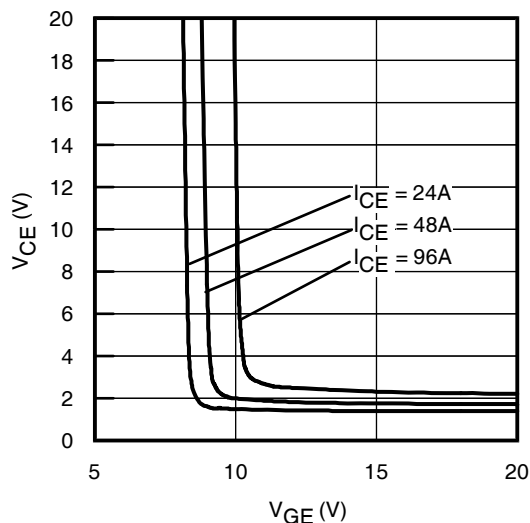


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

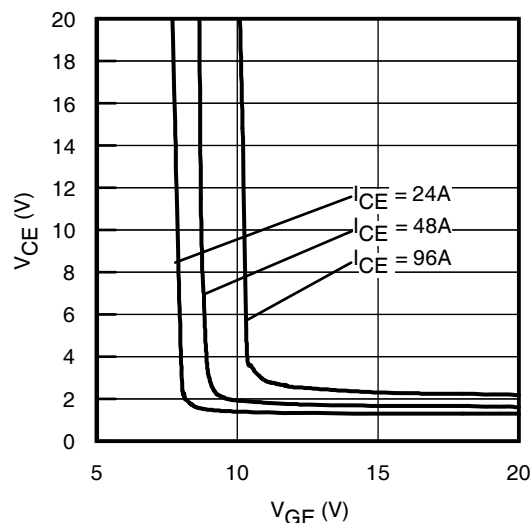


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

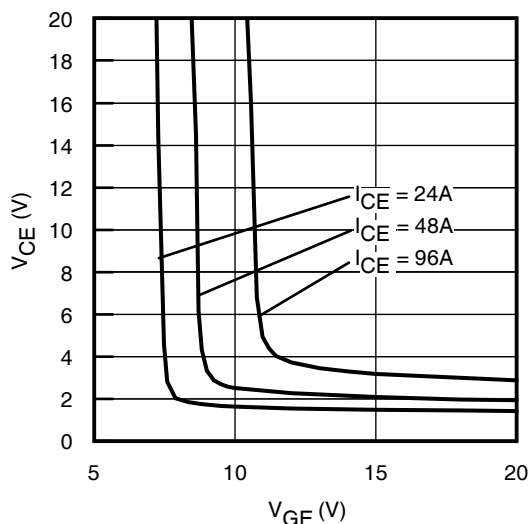


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

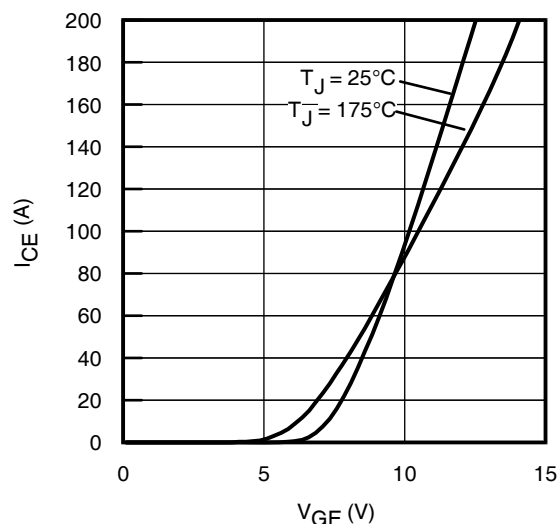
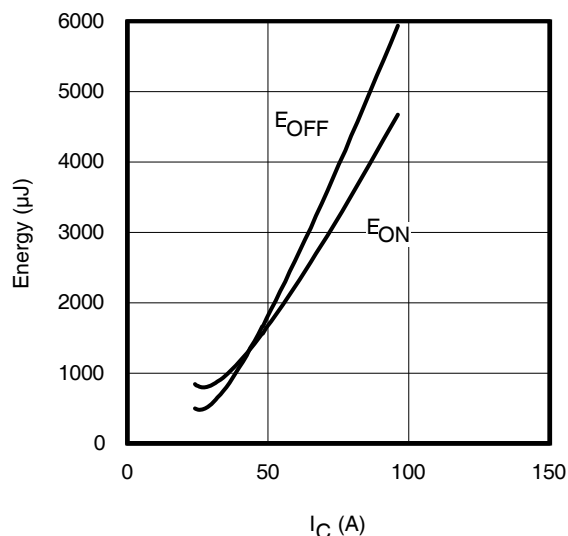
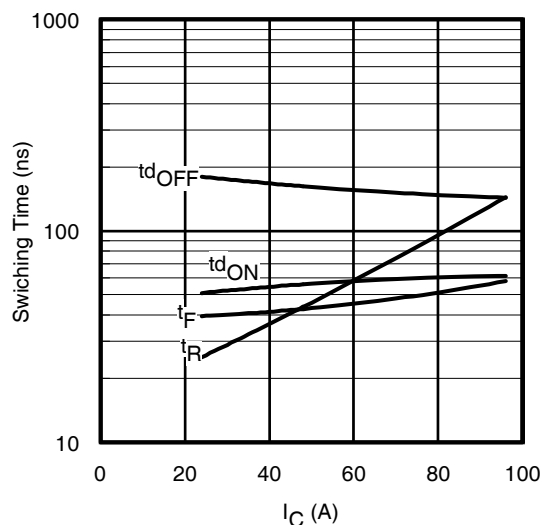
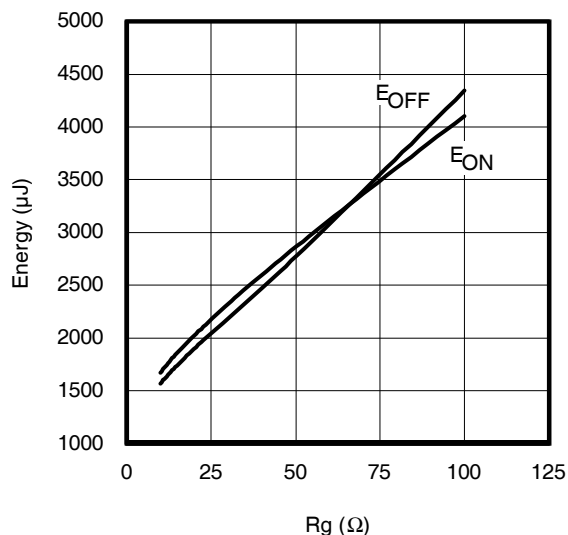
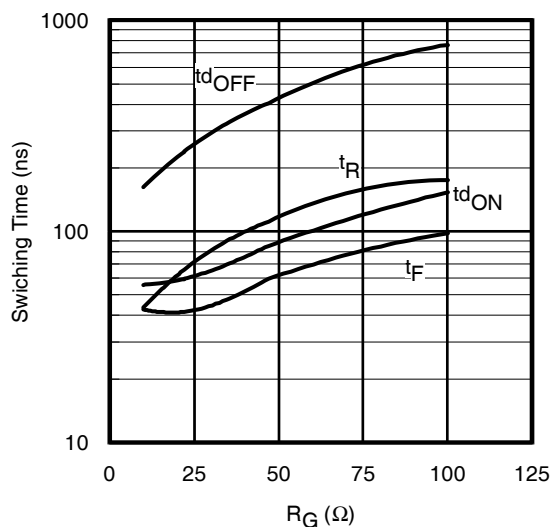
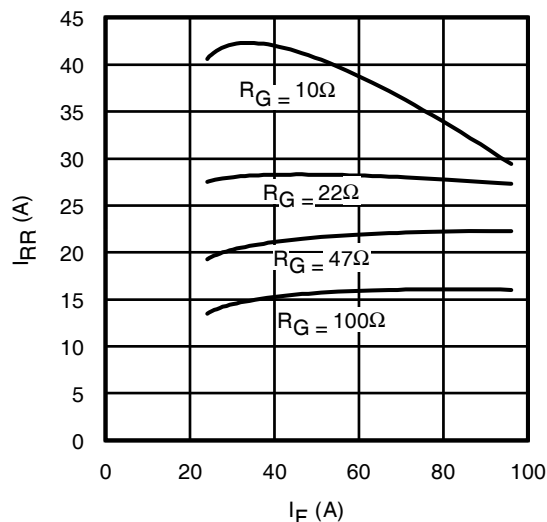
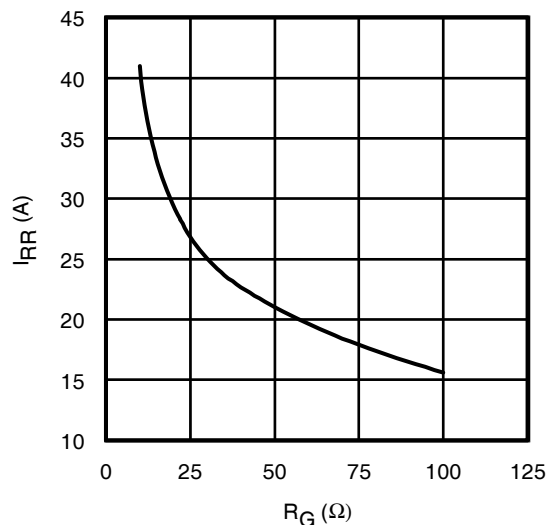


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 10\mu\text{s}$


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 400\text{V}$; $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 400\text{V}$; $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 400\text{V}$; $I_{CE} = 48\text{A}$; $V_{GE} = 15\text{V}$

Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 400\text{V}$; $I_{CE} = 48\text{A}$; $V_{GE} = 15\text{V}$

Fig. 17 - Typ. Diode I_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

Fig. 18 - Typ. Diode I_{RR} vs. R_G
 $T_J = 175^\circ\text{C}$

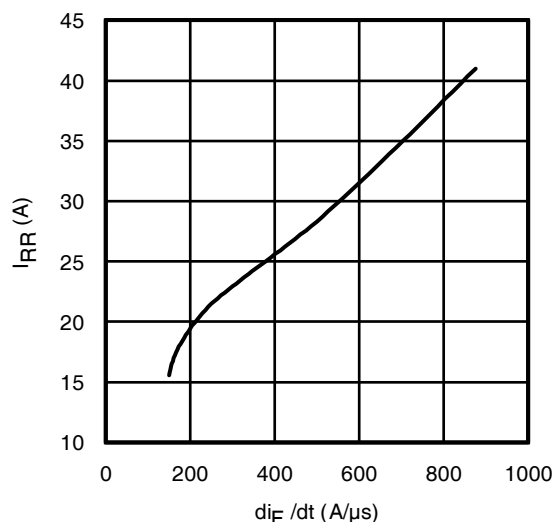


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $I_F = 48A$; $T_J = 175^\circ C$

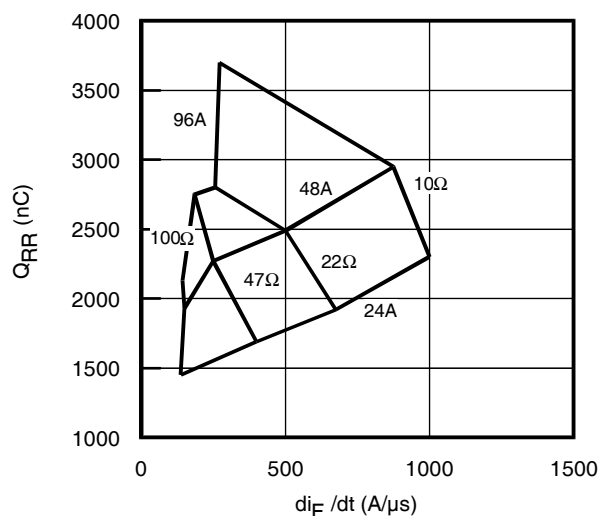


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $T_J = 175^\circ C$

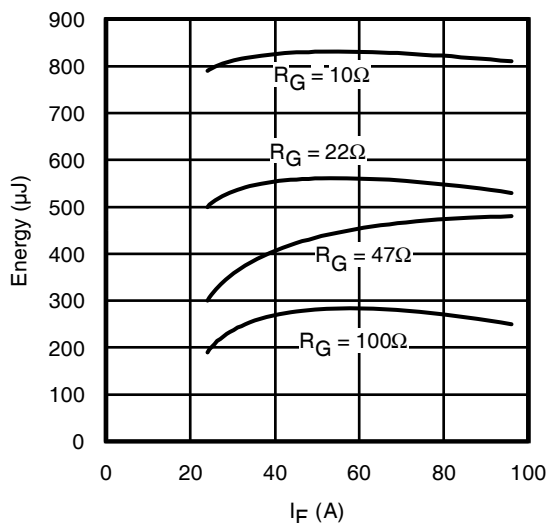


Fig. 21 - Typ. Diode E_{RR} vs. I_F
 $T_J = 175^\circ C$

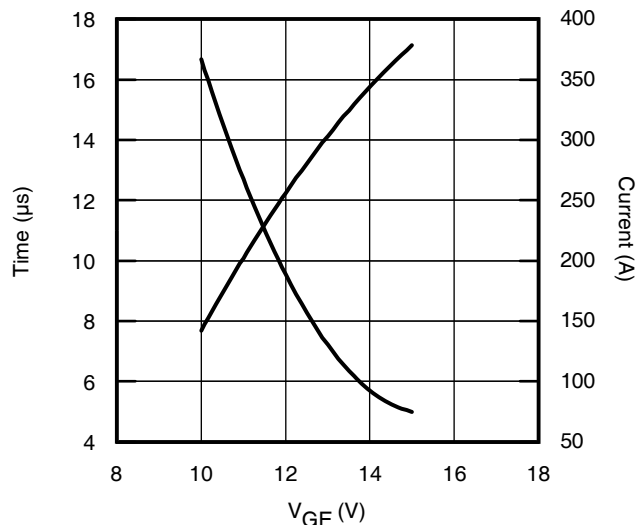


Fig. 22 - V_{GE} vs. Short Circuit Time
 $V_{CC} = 400V$; $T_C = 25^\circ C$

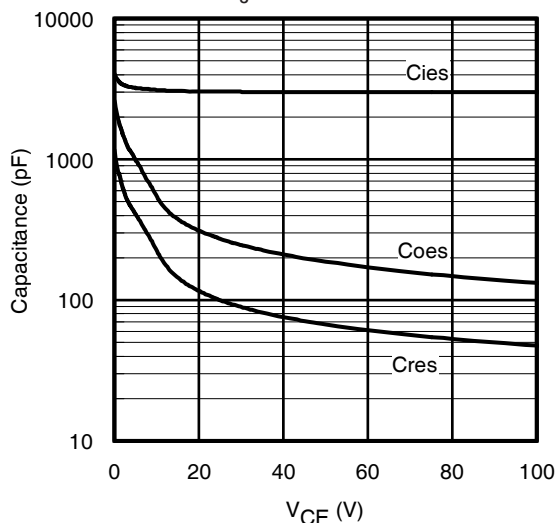


Fig. 23 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

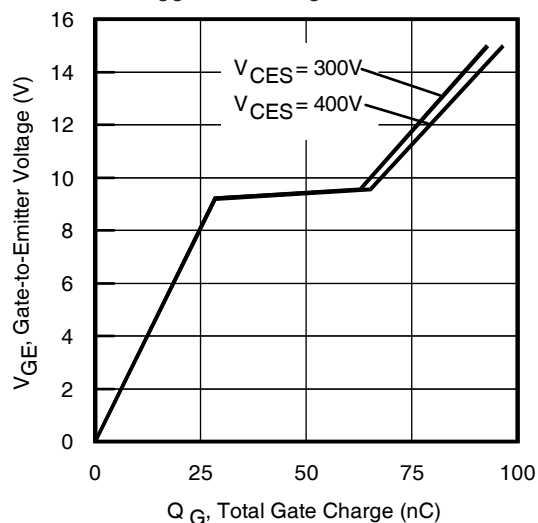


Fig. 24 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 48A$; $L = 600\mu H$

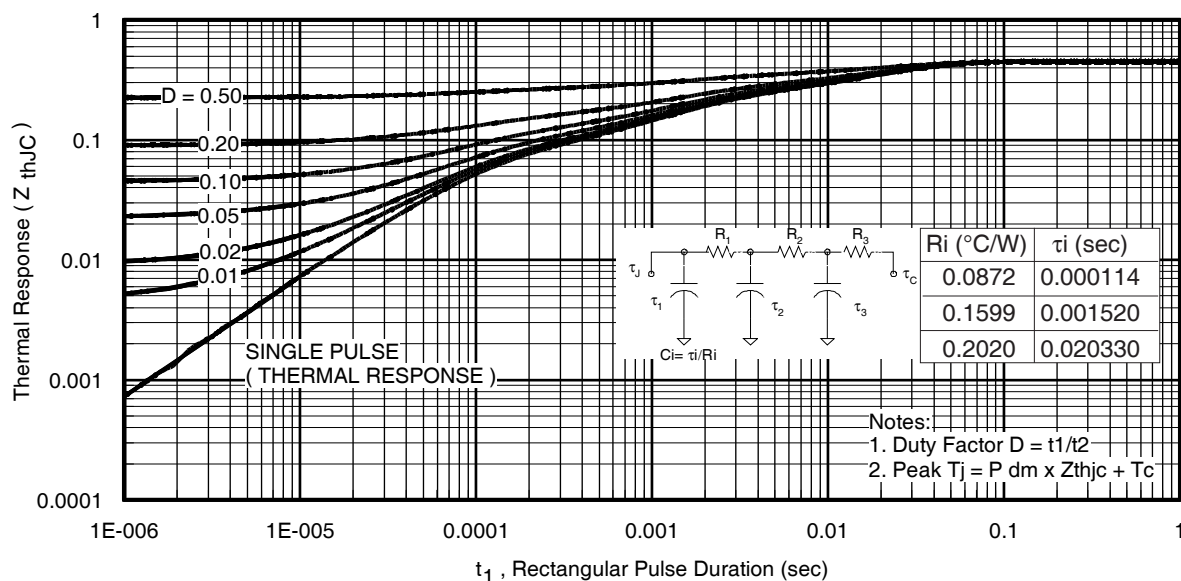


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

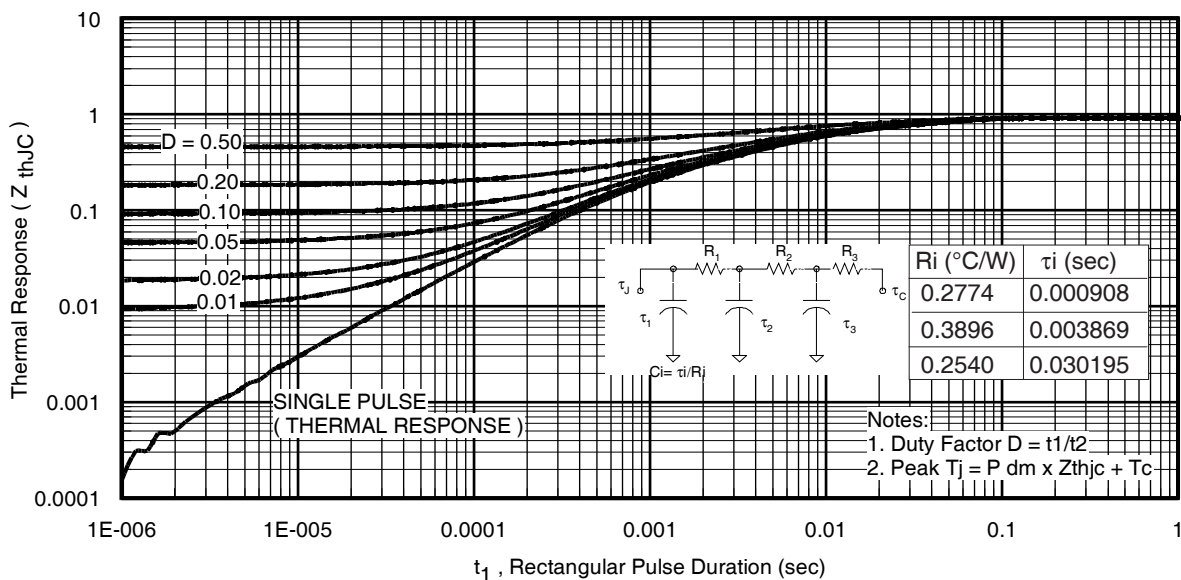


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

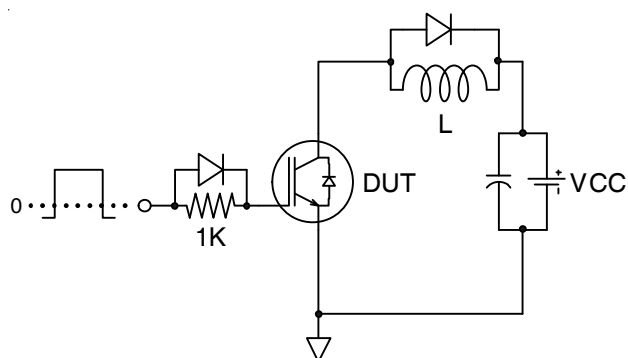


Fig.C.T.1 - Gate Charge Circuit (turn-off)

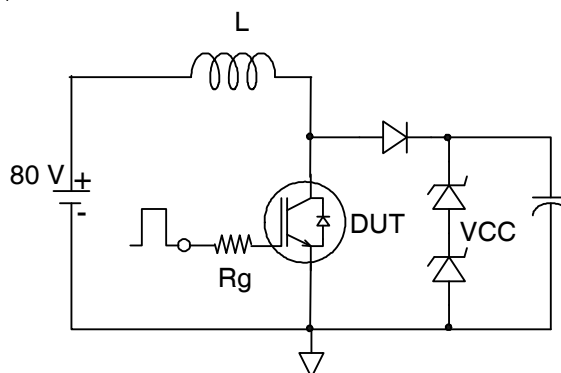


Fig.C.T.2 - RBSOA Circuit

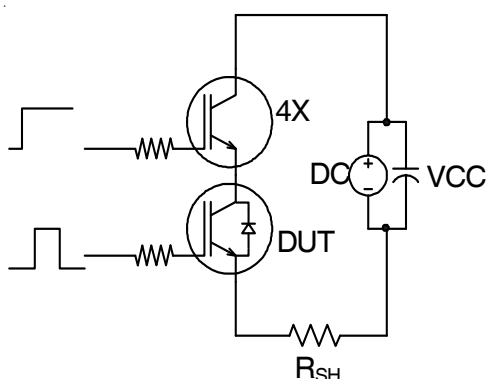


Fig.C.T.3 - S.C. SOA Circuit

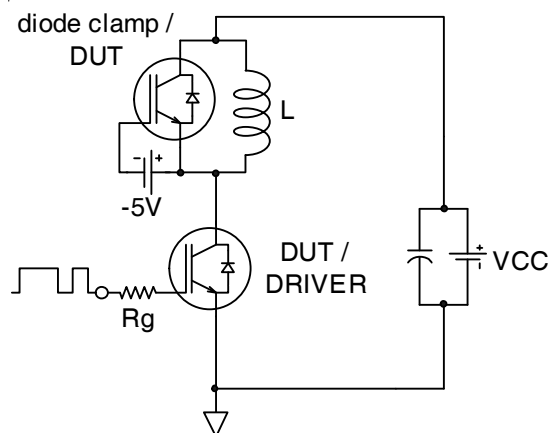


Fig.C.T.4 - Switching Loss Circuit

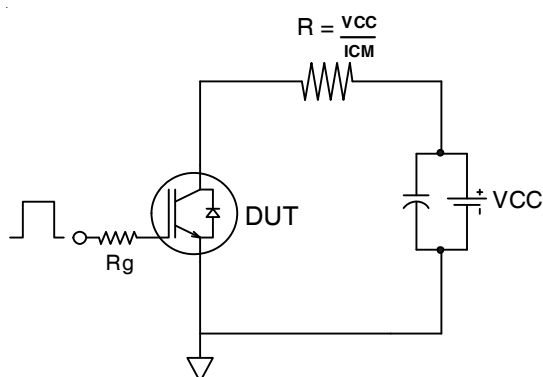


Fig.C.T.5 - Resistive Load Circuit

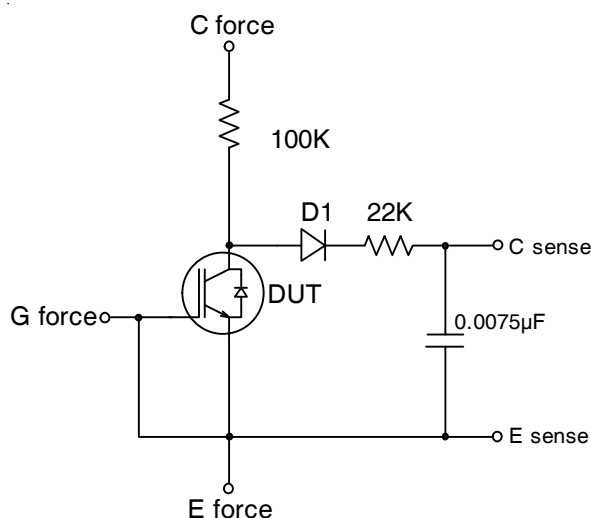


Fig.C.T.6 - BVCES Filter Circuit

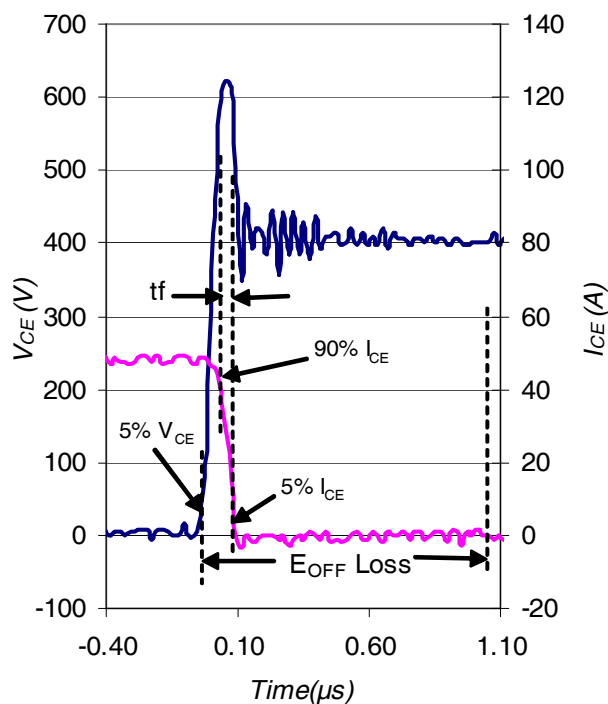


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

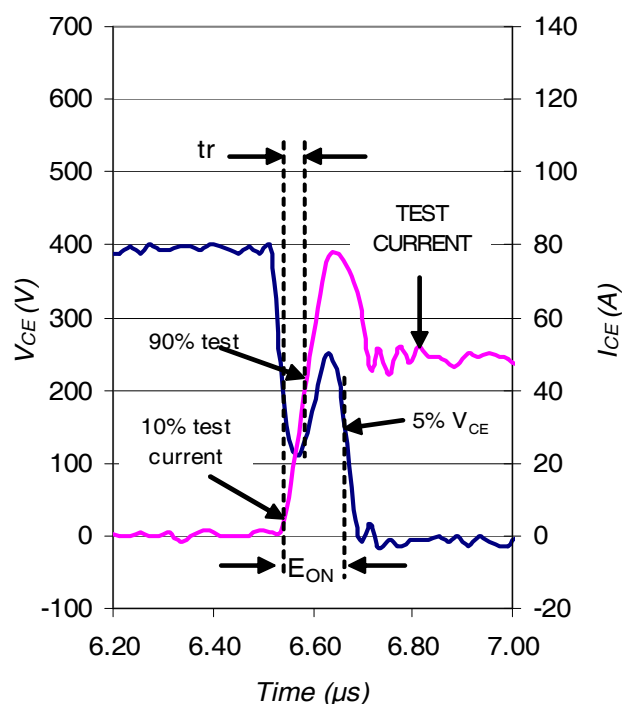


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

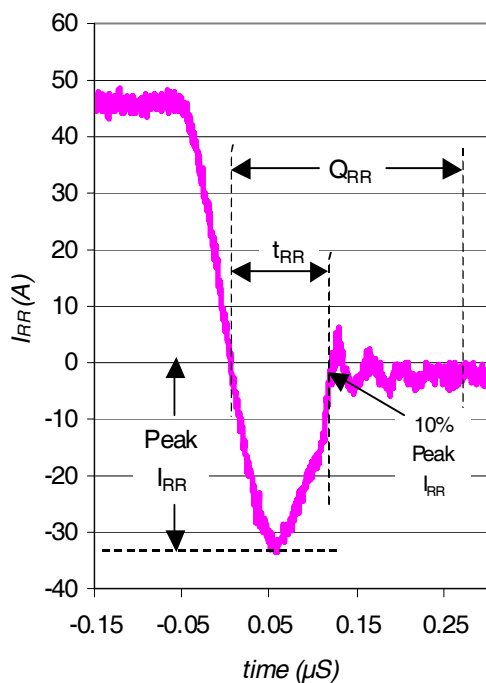


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

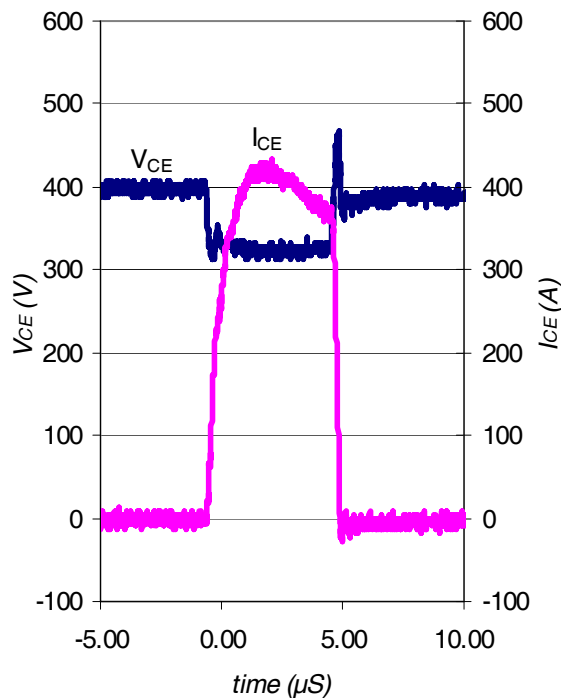
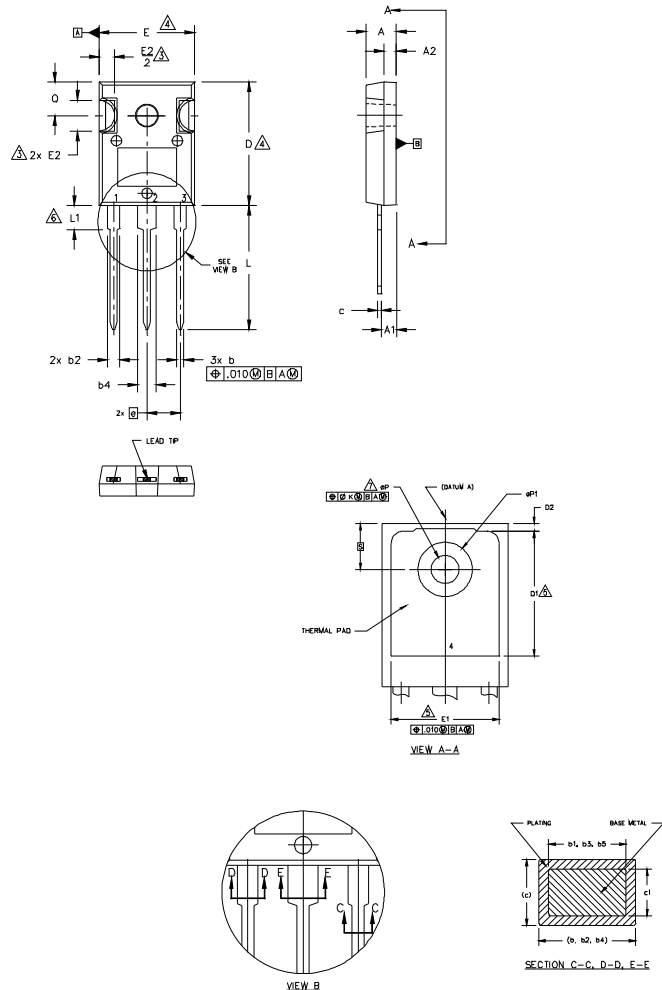


Fig. WF4 - Typ. S.C. Waveform
@ $T_J = 25^\circ\text{C}$ using Fig. CT.3

Dimensions are shown in millimeters (inches)

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

IGBTs, CoPACK

1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

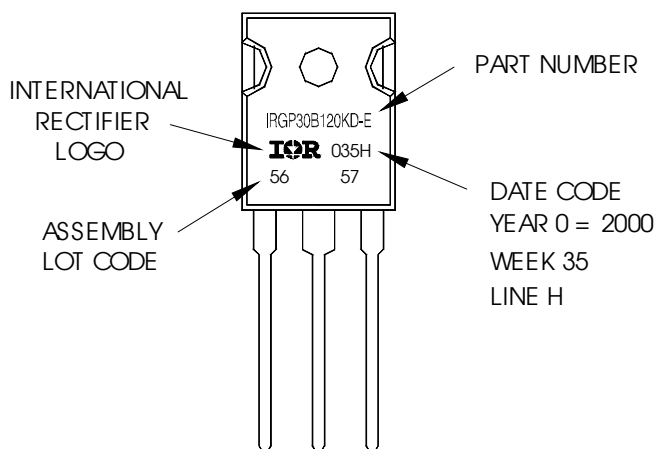
DIODES

1. ANODE/OPEN
2. CATHODE
3. ANODE

TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level		Industrial (per International Rectifier's internal guidelines)	
Moisture Sensitivity Level		TO-247AC	N/A
		TO-247AD	N/A
ESD	Human Body Model	Class 2 (+/- 4000V) ^{††} (per JEDEC JESD22-A114)	
	Charged Device Model	Class IV (+/- 1125V) ^{††} (per JEDEC JESD22-C101)	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Highest passing voltage.

Revision History

Date	Comments
11/17/2014	- Added note ④ to I_{FM} Diode Maximum Forward Current on page 1. - Added note ⑤ to switching losses test condition on page 2.